

# Gunter Semiconductor GmbH

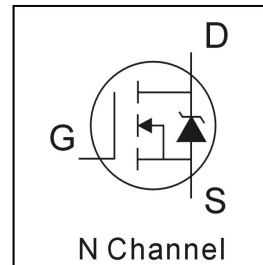
# GFC044

## N Channel Power MOSFET with extremely low RDS(on)

### Chip Specification

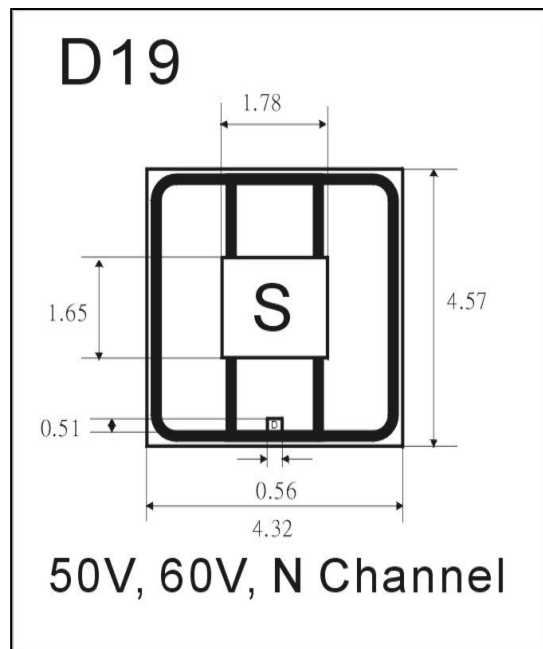
#### General Description:

- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **175°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**
- \* **Extremely low Rds(on)**



#### Mechanical Data:

D19	
Dimension	4.32mm x 4.57mm
Thickness:	400 μm
Metallization:	
Top :	Al
Backside :	CrNiAg / Au
Suggested Bonding Conditions:	
Die Mounting:	Solder Perform
95/5 PbSn or 92.5/2.5/5 PbAgIn	
Source Bonding Wire:	20 mil Al



#### Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	60	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.028	Ω	VGS=10V, ID=25A
Continuous Drain current ( in target package)	ID@25°C	41	A	VGS=10V
Continuous Drain current ( in target package)	ID@100°C	29	A	VGS=10V
Operation Junction	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

#### Target Device: IRFZ44

TO-263AB

Pd 2 W @Ta=25°C

Pd 83 W @Tc=25°C